

2N5432
N-CHANNEL SILICON JUNCTION
FIELD-EFFECT TRANSISTORS

***ABSOLUTE MAXIMUM RATINGS (25°C)**

Reverse Gate-Drain or Gate-Source Voltage	-25 V
Gate Current	100 mA
Drain Current	400 mA
Total Device Dissipation at 25°C Free-Air Temperature	300 mW
Storage Temperature	-65 to +150°C
Lead Temperature 1/16" from Case for 10 sec	300°C

***ELECTRICAL CHARACTERISTICS (unless otherwise noted)**

Characteristic	Test Conditions	2N5432		Unit
		Min	Max	
BV_{GSS} Gate Source Breakdown Voltage	$I_G = -1 \mu A, V_{DS} = 0$	-25		V
I_{GSS} Gate Reverse Current	$V_{GS} = -15 V, V_{DS} = 0$ 25°C		-200	pA
	150°C		-200	nA
$I_{D(OFF)}$ Drain Cutoff Current	$V_{DS} = 5 V, V_{GS} = -10 V$ 25°C		200	pA
	150°C		200	nA
V_P Gate-Source Pinch-Off Voltage	$V_{DS} = 5 V, I_D = 3 nA$	-4	-10	V
I_{DSS} Drain Current at Zero Gate Voltage (Note 3)	$V_{DS} = 15 V, V_{GS} = 0$	150		mA
r_{DS} Static Drain-Source ON Resistance	$V_{GS} = 0, I_D = 10 mA$	2	5	ohm
$V_{DS(ON)}$ Drain-Source ON Voltage	$V_{GS} = 0, I_D = 10 mA$		50	mV
r_{ds} Small-Signal Drain-Source ON Resistance	$V_{GS} = 0, I_D = 0, f = 1 kHz$		5	ohm
C_{iss} Common-Source Input Capacitance	$V_{DS} = 0, V_{GS} = -10 V, f = 1 MHz$		30	pF
C_{rss} Common Source Reverse Transfer Capacitance	$V_{DS} = 0, V_{GS} = -10 V, f = 1 MHz$		15	pF

TO-52

